COMPLEMENTARY PAIR ENHANCEMENT MODE MOSFET

Product Summary

Device	$V_{(BR)DSS}$	$R_{DS(on)}$ max	I_D Max T_A = +25°C
Q2	30V	21mΩ @ V_{GS} = 10V	8.5A
		32mΩ @ V_{GS} = 4.5V	7.2A
Q1	-30V	39mΩ @ V_{GS} = -10V	-7A
		53mΩ @ V_{GS} = -4.5V	-5.6A

Description and

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

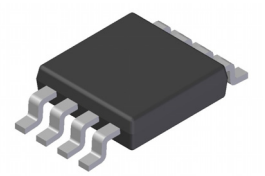
- Power Management Functions
- Analog Switch
- Load Switch

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

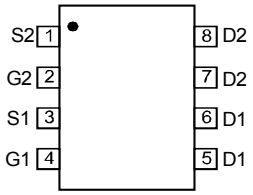
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072 grams (approximate)

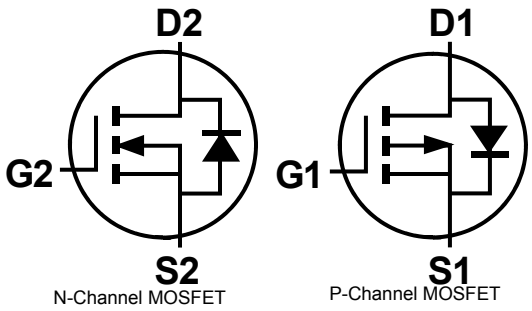


Top View

SO-8



Top View

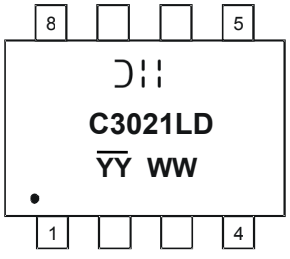


Ordering Information (Note 4)

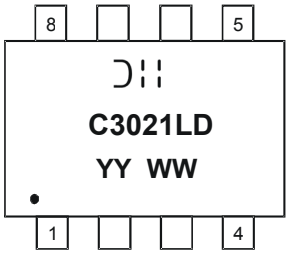
Part Number	Case	Packaging
DMC3021LSD-13	SO-8	2500/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

= Manufacturer's Marking
C3021LD = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 14 = 2014)
WW = Week (01 - 53)
YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Maximum Ratings N-CHANNEL – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5)	Steady State	T_A = +25°C T_A = +85°C	I_D	8.5 7.1	A
Pulsed Drain Current (Note 6)			I_{DM}	26	A

Maximum Ratings P-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5)	Steady State	T_A = +25°C T_A = +85°C	I_D	-7.0 -4.5	A
Pulsed Drain Current (Note 6)			I_{DM}	-25	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	50	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics N-CHANNEL – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1.0	μA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1	1.45	2.1	V	V_{DS} = V_{GS}, I_C = 250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	— —	14 18	21 32	mΩ	V_{GS} = 10V, I_C = 7A V_{GS} = 4.5V, I_C = 5.6A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	8.1	—	S	V_{DS} = 5V, I_C = 7A
Diode Forward Voltage (Note 7)	V_{SD}	—	0.7	1.0	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	767	—	pF	V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	110	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	105	—	pF	
Gate Resistance	R_g	—	1.4	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	7.8	—	nC	V_{DS} = 15V, I_D = 9A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	16.1	—	nC	
Gate-Source Charge	Q_{gs}	—	1.8	—	nC	
Gate-Drain Charge	Q_{gd}	—	2.5	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	5.0	—	ns	V_{GS} = 10V, V_{DS} = 15V, R_G = 6Ω , I_D = 1A
Turn-On Rise Time	t_r	—	4.5	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	26.3	—	ns	
Turn-Off Fall Time	t_f	—	8.55	—	ns	

Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Repetitive rating, pulse width limited by junction temperature.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

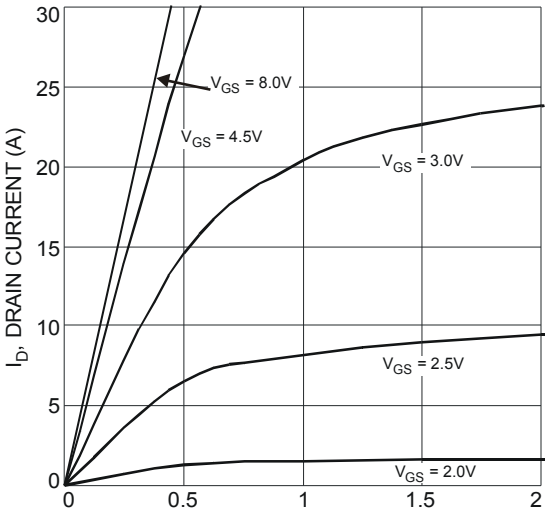


Fig. 1 Typical Output Characteristics

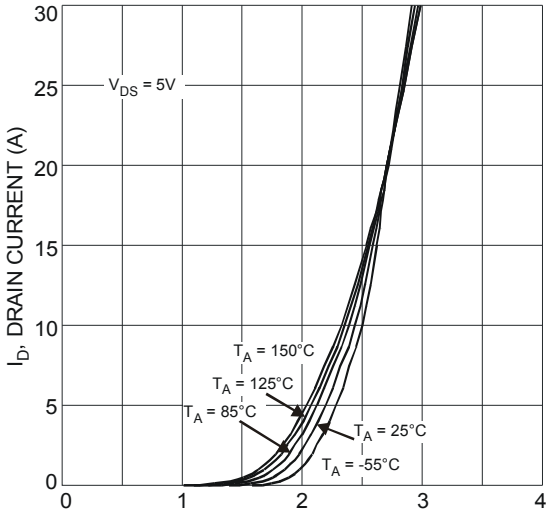


Fig. 2 Typical Transfer Characteristics

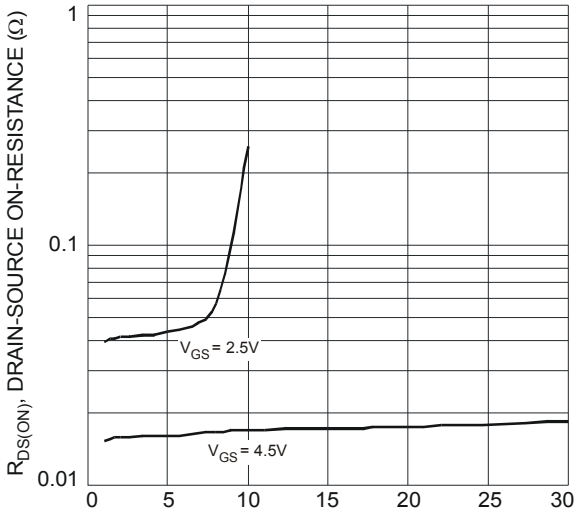


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

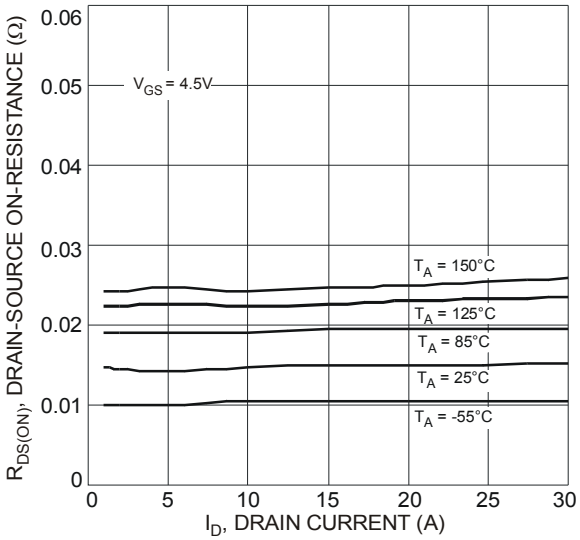


Fig. 4 Typical Drain-Source On-Resistance
vs. Drain Current and Temperature

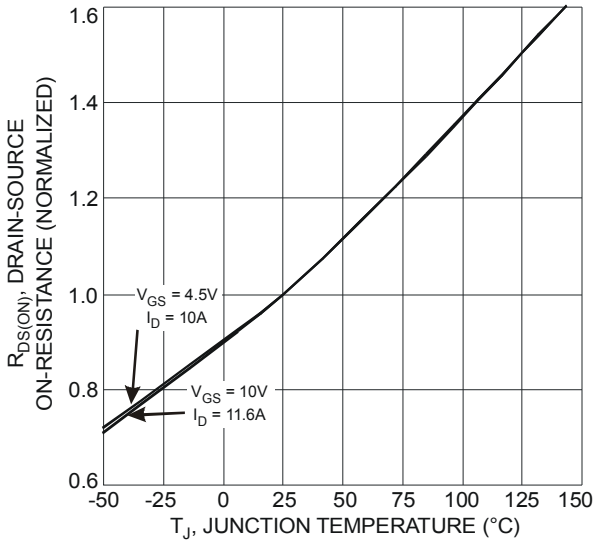


Fig. 5 On-Resistance Variation with Temperature

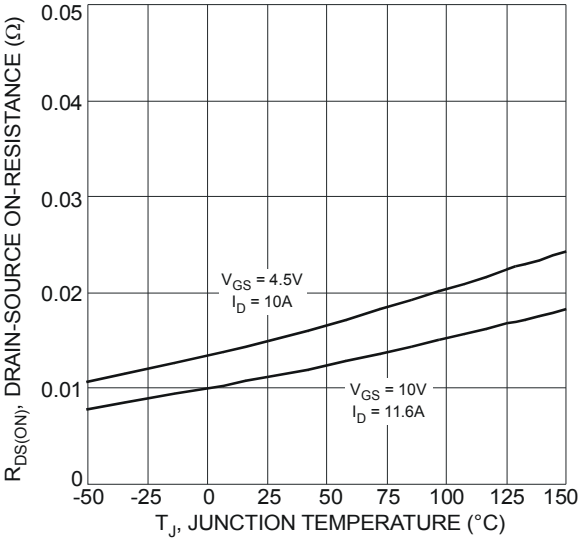


Fig. 6 On-Resistance Variation with Temperature

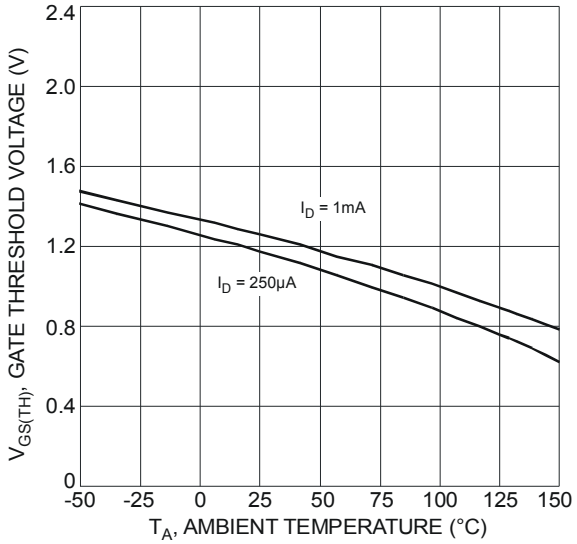


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

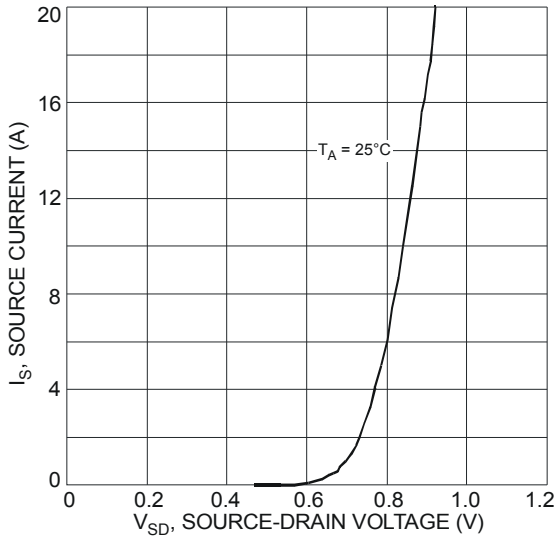


Fig. 8 Diode Forward Voltage vs. Current

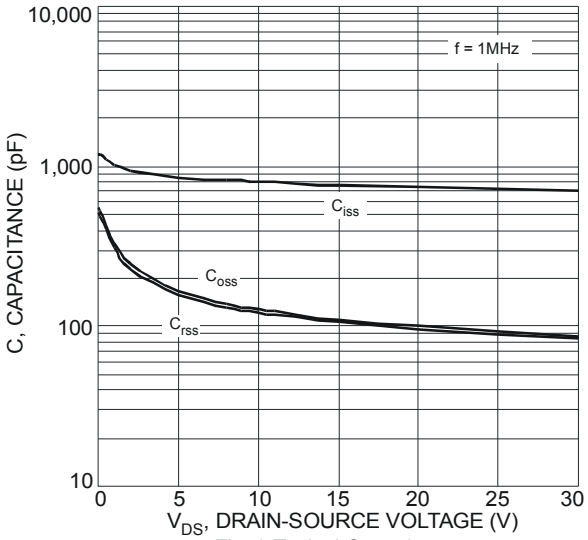


Fig. 9 Typical Capacitance

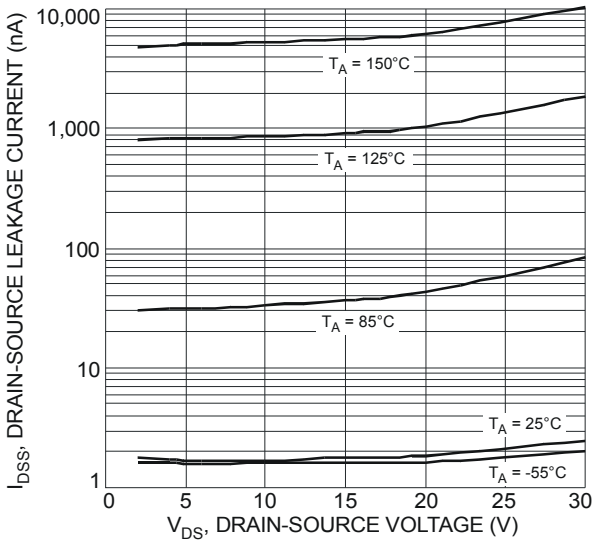


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

Electrical Characteristics P-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1.0	μA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-1	-1.7	-2.2	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	30	39	mΩ	V_{GS} = -10V, I_D = -4.3A
		—	42	53		V_{GS} = -4.5V, I_D = -3.7A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	7	—	S	V_{DS} = -5V, I_D = -4.3A
Diode Forward Voltage (Note 7)	V_{SD}	—	-0.75	-1.0	V	V_{GS} = 0V, I_S = -1.7A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1002	—	pF	V_{DS} = -10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	125	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	118	—	pF	
Gate Resistance	R_g	—	13	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	10.1	—	nC	V_{DS} = -15V, I_D = -6A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	21.1	—	nC	
Gate-Source Charge	Q_{gs}	—	2.8	—	nC	
Gate-Drain Charge	Q_{gd}	—	3.2	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	10.1	—	ns	V_{GS} = -10V, V_{DS} = -15V, R_G = 6Ω , I_D = -1A
Turn-On Rise Time	t_r	—	6.5	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	50.1	—	ns	
Turn-Off Fall Time	t_f	—	22.2	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

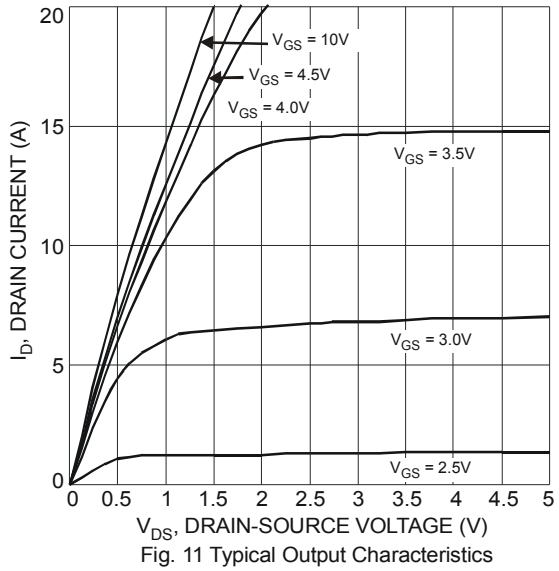


Fig. 11 Typical Output Characteristics

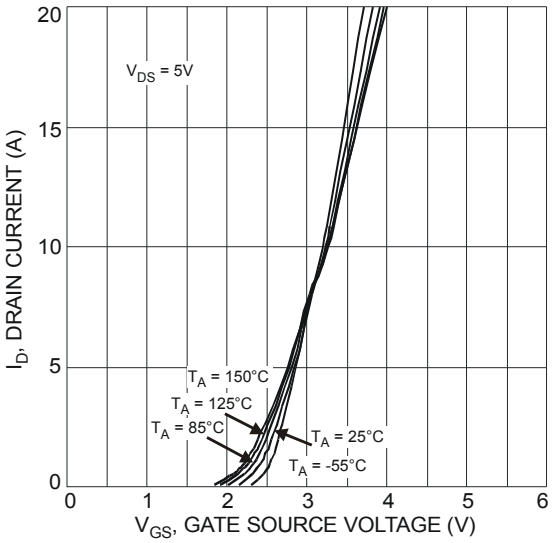


Fig. 12 Typical Transfer Characteristics

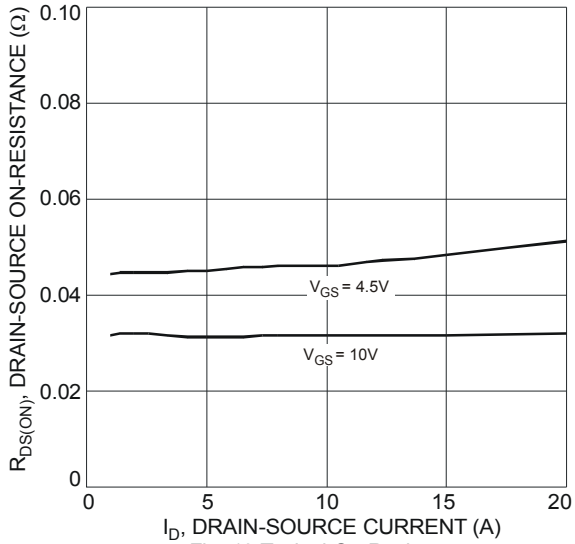


Fig. 13 Typical On-Resistance vs. Drain Current and Gate Voltage

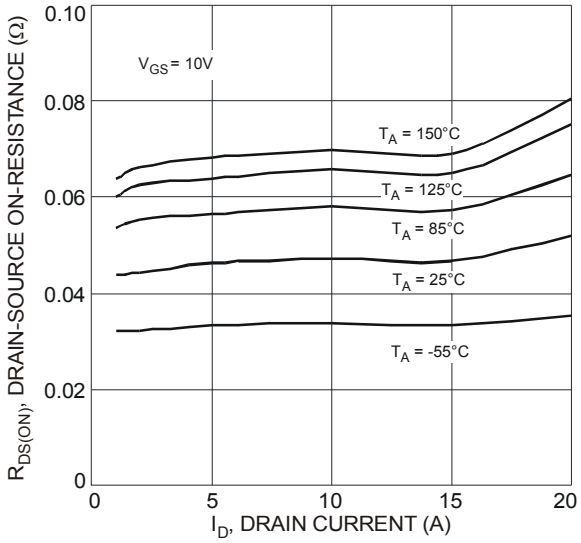


Fig. 14 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

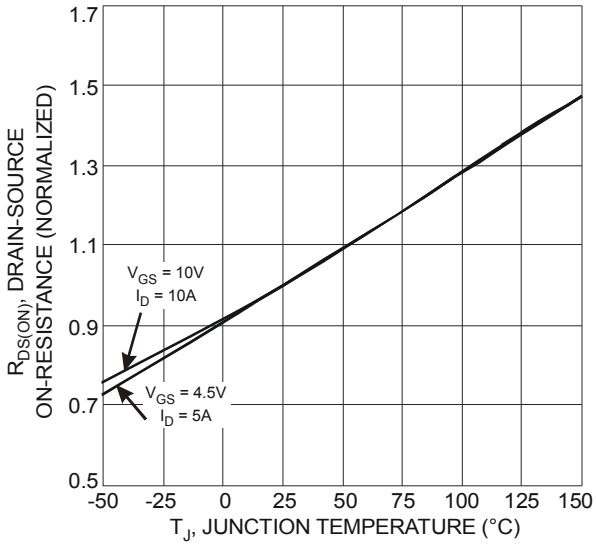


Fig. 15 On-Resistance Variation with Temperature

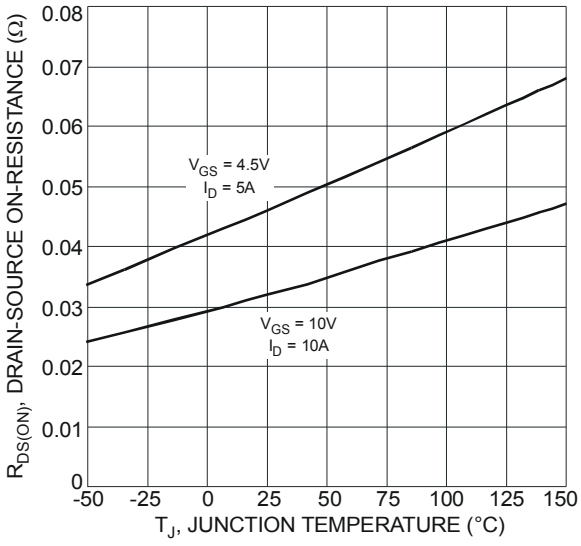


Fig. 16 On-Resistance Variation with Temperature

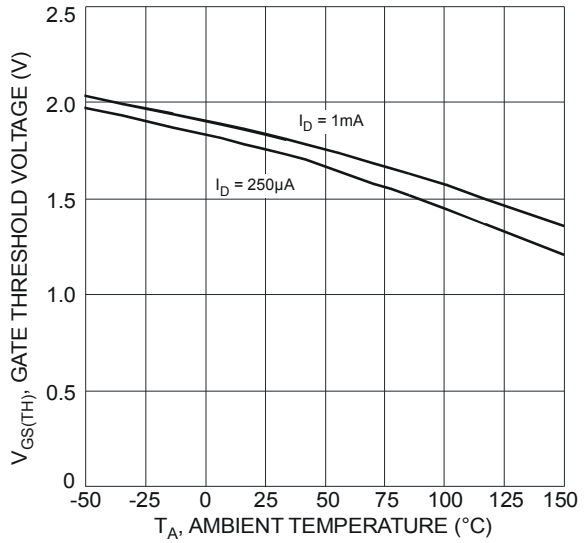


Fig. 17 Gate Threshold Variation vs. Ambient Temperature

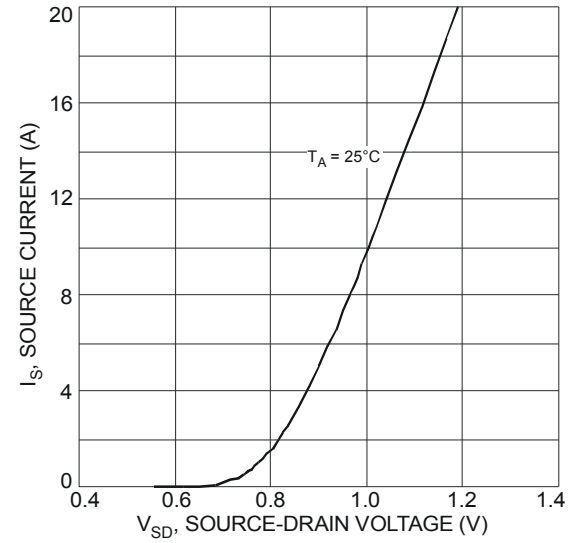


Fig. 18 Diode Forward Voltage vs. Current

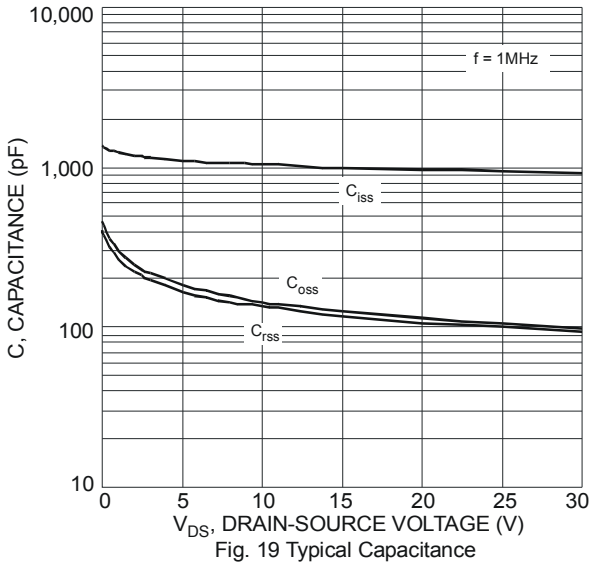


Fig. 19 Typical Capacitance

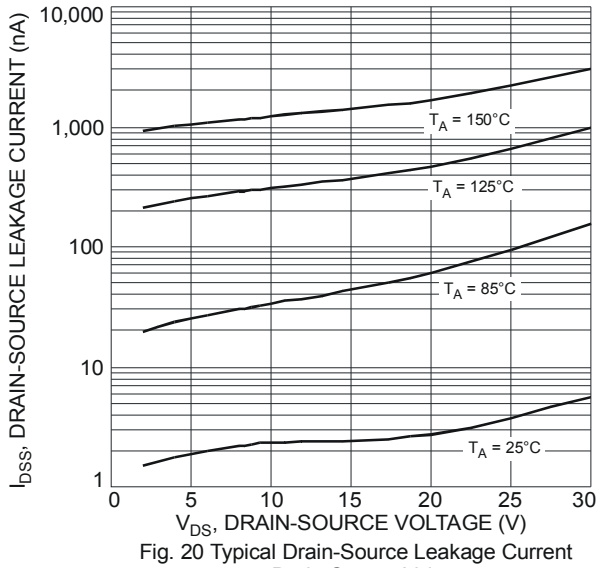
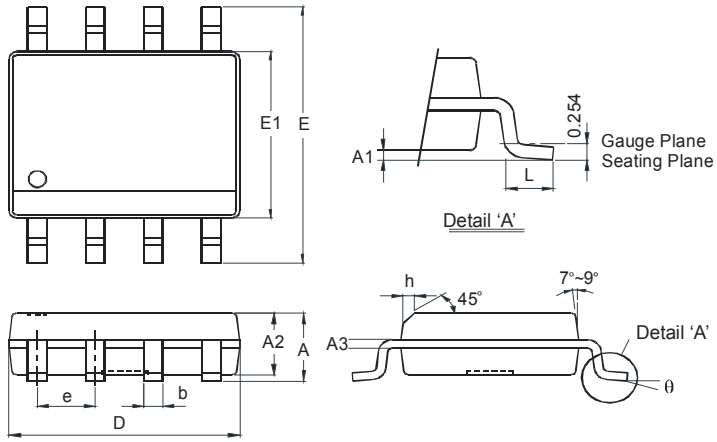


Fig. 20 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

Package Outline Dimensions

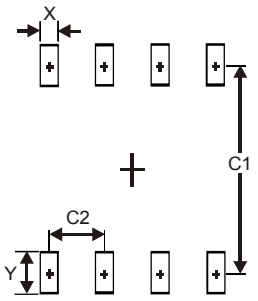
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8		
Dim	**Min**	**Max**
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

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